

Insulated Gate Bi-Polar Transistor

Type T0340VB45G

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{CES}	Collector – emitter voltage	4500	V
$V_{DC\ link}$	Permanent DC voltage for 100 FIT failure rate.	2800	V
V_{GES}	Peak gate – emitter voltage	± 20	V

	RATINGS	MAXIMUM LIMITS	UNITS
$I_{C(DC)}$	DC collector current, IGBT	340	A
I_{CRM}	Repetitive peak collector current, $t_p=1ms$, IGBT	680	A
$I_{F(DC)}$	Continuous DC forward current, Diode	340	A
I_{FRM}	Repetitive peak forward current, $t_p=1ms$, Diode	680	A
I_{FSM}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}=60\%V_{RRM}$, Diode (Note 4)	2060	A
I_{FSM2}	Peak non-repetitive surge $t_p=10ms$, $V_{RM}\leq 10V$, Diode (Note 4)	2280	A
P_{MAX}	Maximum power dissipation, IGBT (Note 2)	2.7	kW
$(di/dt)_{cr}$	Critical diode di/dt (note 3)	500	A/ μs
T_j	Operating temperature range.	-40 to +125	$^{\circ}C$
T_{stg}	Storage temperature range.	-40 to +125	$^{\circ}C$

Notes: -

- 1) Unless otherwise indicated $T_j = 125^{\circ}C$.
- 2) $T_{sink} = 25^{\circ}C$, double side cooled.
- 3) Maximum commutation loop inductance 200nH.
- 4) Half-sinewave, $125^{\circ}C$ T_j initial.

Characteristics

IGBT Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _{CE(sat)}	Collector – emitter saturation voltage	-	2.75	3.2	I _C = 340A, V _{GE} = 15V, T _j = 25°C	V
		-	3.50	3.9	I _C = 340A, V _{GE} = 15V	V
V _{T0}	Threshold voltage	-	-	2.18	Current range: 340 – 1020A	V
r _T	Slope resistance	-	-	5.05		mΩ
V _{GE(TH)}	Gate threshold voltage	-	5.2	-	V _{CE} = V _{GE} , I _C = 35mA	V
I _{CES}	Collector – emitter cut-off current	-	10	25	V _{CE} = V _{CES} , V _{GE} = 0V	mA
I _{GES}	Gate leakage current	-	-	±7	V _{GE} = ±20V	µA
C _{ies}	Input capacitance	-	60	-	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	nF
t _{d(on)}	Turn-on delay time	-	3.7	-	I _C = 340A, V _{CE} = 2800V, di/dt = 500A/µs	µs
t _{r(V)}	Rise time	-	3.2	-		µs
Q _{g(on)}	Turn-on gate charge	-	6.5	-	V _{GE} = ±15V, L _s = 200nH	µC
E _{on}	Turn-on energy	-	2.9	-	R _{g(ON)} = 18Ω, R _{g(OFF)} = 20Ω, C _{GE} = 47nF	J
t _{d(off)}	Turn-off delay time	-	2.2	-	Integral diode used as freewheel diode (Note 3 & 4)	µs
t _{r(I)}	Fall time	-	2.6	-		µs
Q _{g(off)}	Turn-off gate charge	-	10	-		µC
E _{off}	Turn-off energy	-	1.4	-		J
I _{SC}	Short circuit current	-	1100	-	V _{GE} = +15V, V _{CC} = 2800V, V _{CEmax} ≤ V _{CES} , t _p ≤ 10µs	A

Diode Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
V _F	Forward voltage	-	3.3	3.6	I _F = 340A, T _j = 25°C	V
		-	3.45	3.8	I _F = 340A	V
V _{T0}	Threshold voltage	-	-	2.88	Current range 340-1020A	V
r _T	Slope resistance	-	-	2.72		mΩ
I _{rm}	Peak reverse recovery current	-	220	-	I _F = 340A, V _{GE} = -15V, di/dt = 500A/µs	A
Q _{rr}	Recovered charge	-	500	-		µC
t _{rr}	Reverse recovery time, 50% chord	-	3.2	-		µs
E _r	Reverse recovery energy	-	0.4	-		J

Thermal Characteristics

	PARAMETER	MIN	TYP	MAX	TEST CONDITIONS	UNITS
R _{thJK}	Thermal resistance junction to sink, IGBT	-	-	36.4	Double side cooled	K/kW
		-	-	94.3	Collector side cooled	K/kW
		-	-	59.4	Emitter side cooled	K/kW
R _{thJK}	Thermal resistance junction to sink, Diode	-	-	57.6	Double side cooled	K/kW
		-	-	88.2	Cathode side cooled	K/kW
		-	-	166	Anode side cooled	K/kW
F	Mounting force	12	-	16	Note 2	kN
W _t	Weight	-	0.65	-		kg

Notes:-

- 1) Unless otherwise indicated T_j = 125°C.
- 2) Consult application note 2008AN01 for detailed mounting requirements
- 3) C_{GE} is additional gate – emitter capacitance added to output of gate drive
- 4) Figures 6 to 9 are obtained using integral diode as freewheeling diode

Curves

Figure 1 – Typical collector-emitter saturation voltage characteristics

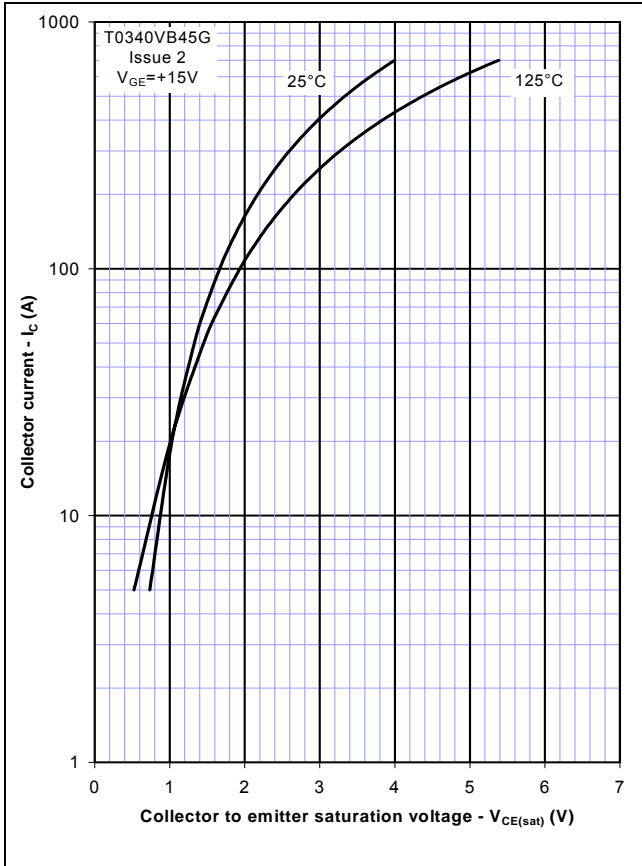


Figure 2 – Typical output characteristic

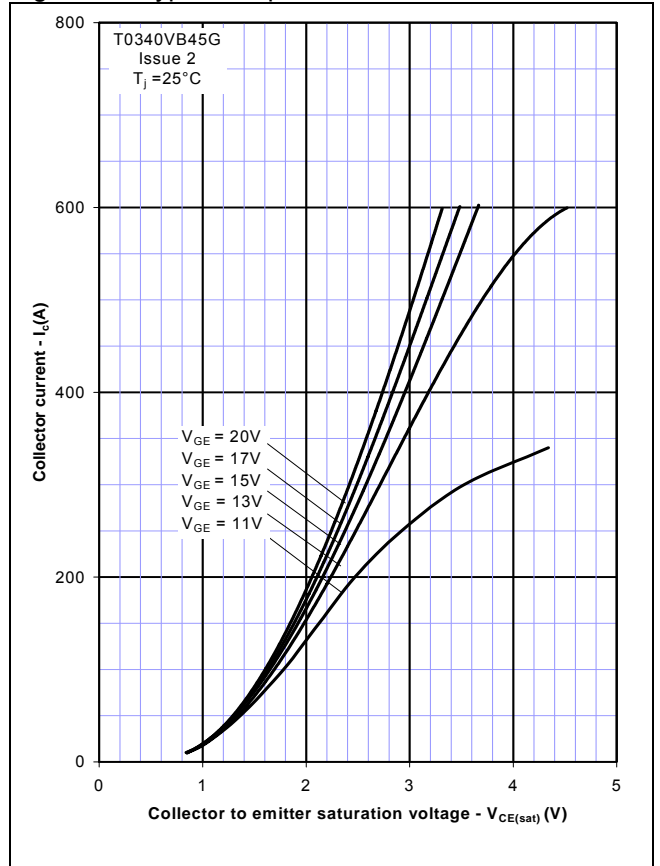


Figure 3 – Typical output characteristic

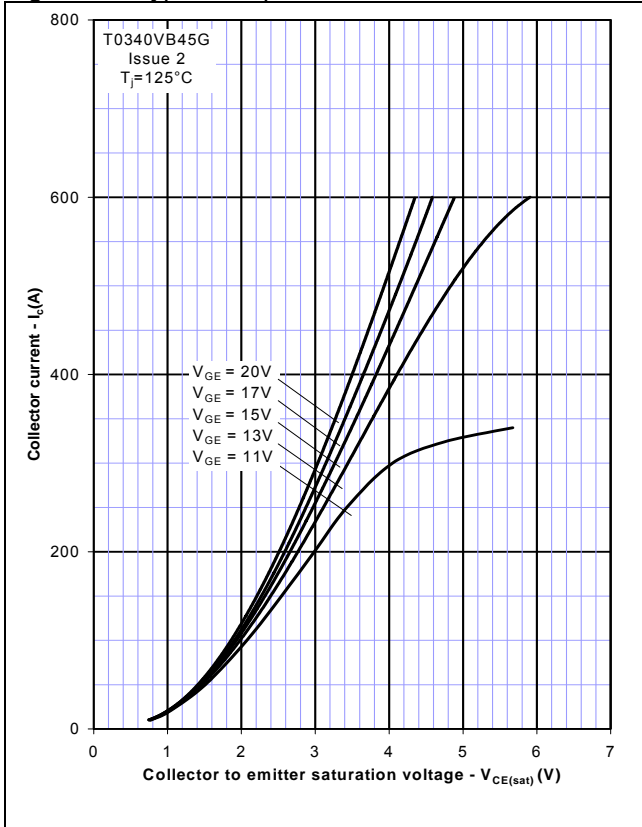


Figure 4 – Typical turn-on delay time vs gate resistance

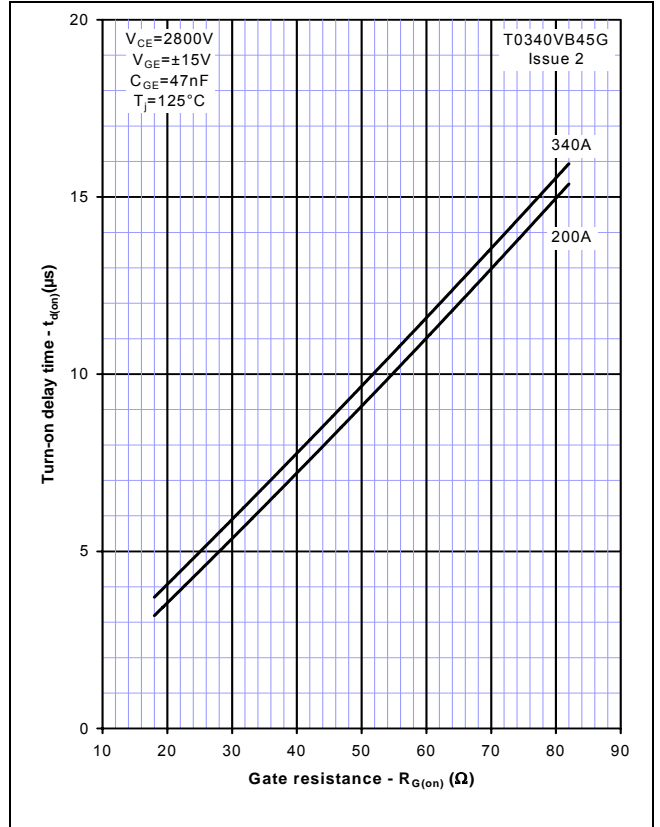


Figure 5 – Typical turn-off delay time vs. gate resistance

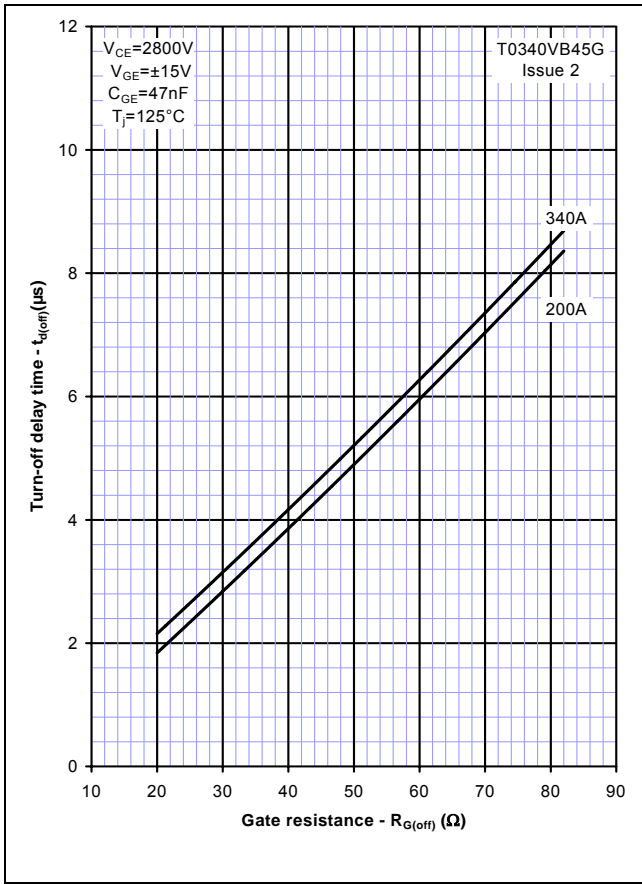


Figure 6 – Typical turn-on energy vs. collector current

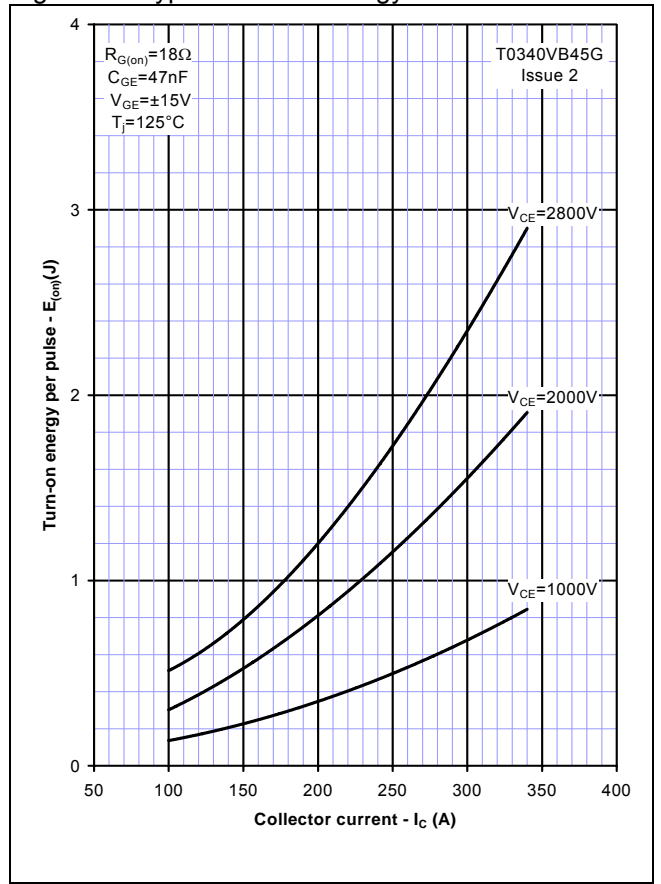


Figure 7 – Typical turn-on energy vs. di/dt

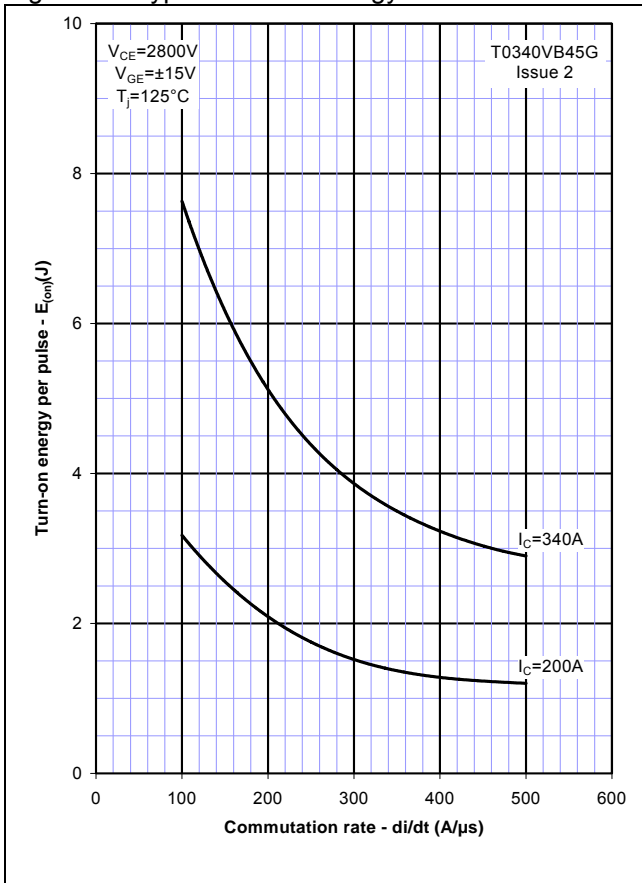


Figure 8 – Typical turn-off energy vs. collector current

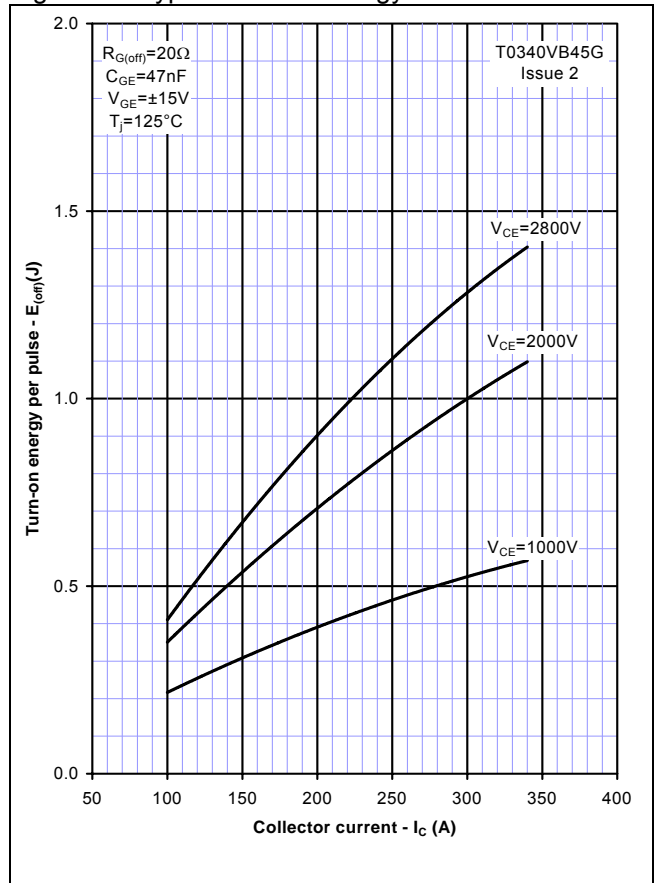


Figure 9 – Turn-off energy vs voltage

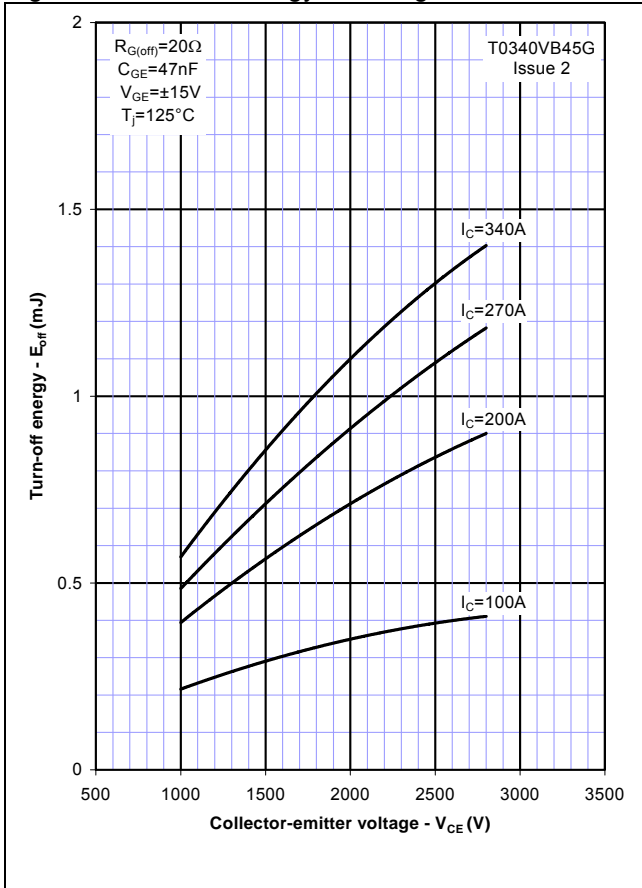


Figure 10 – Safe operating area

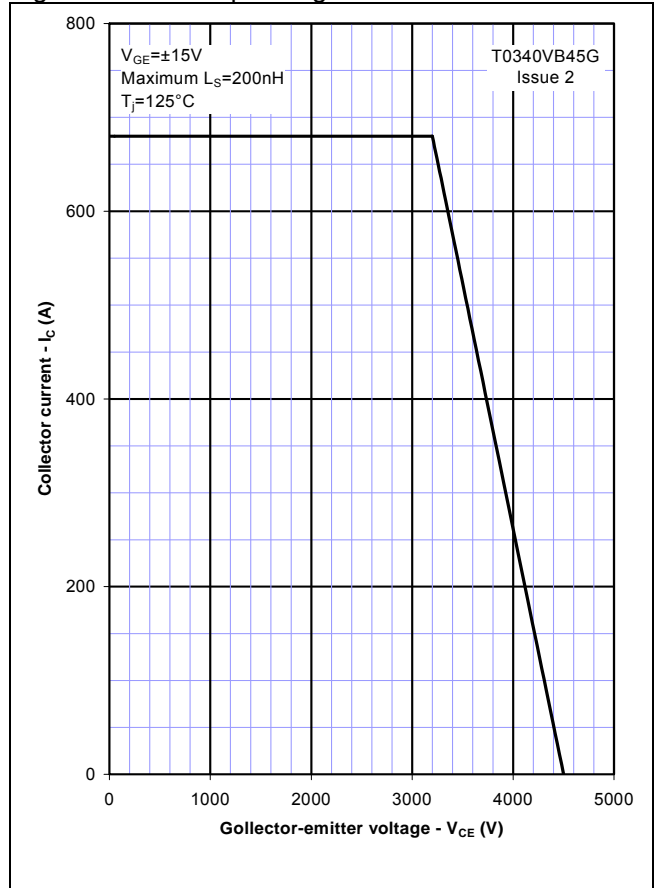


Figure 11 – Typical diode forward characteristics

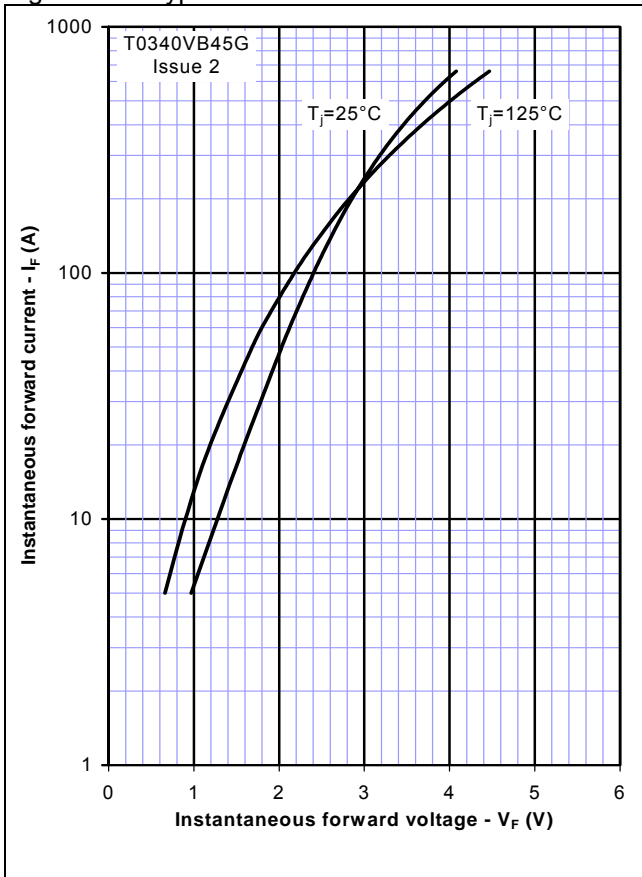


Figure 12 – Typical recovered charge

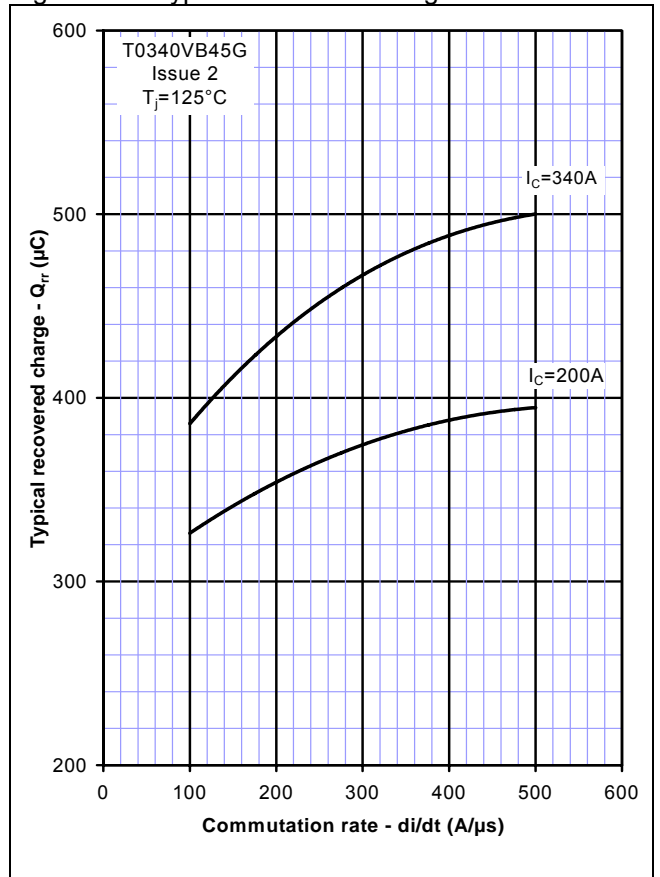


Figure 13 – Typical reverse recovery current

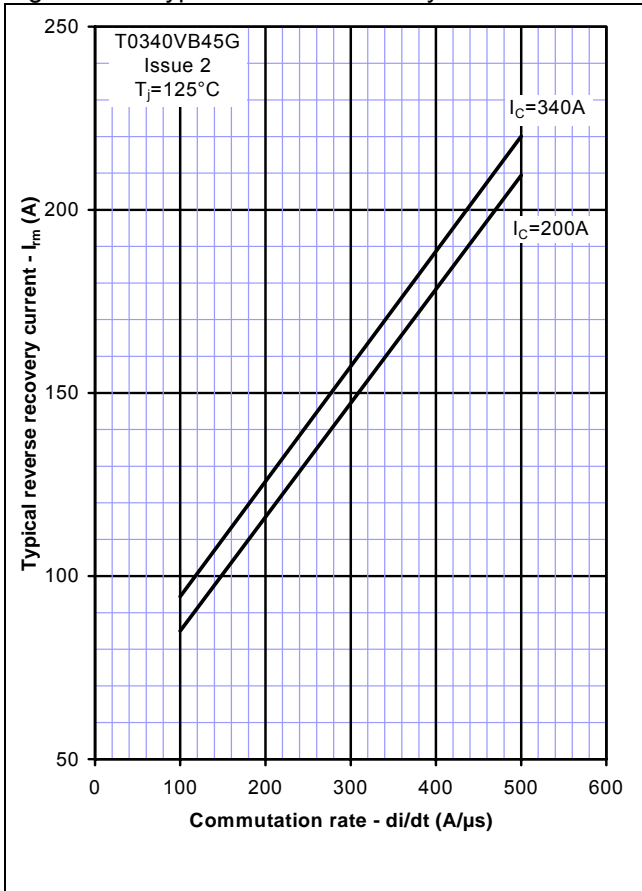


Figure 14 – Typical reverse recovery time

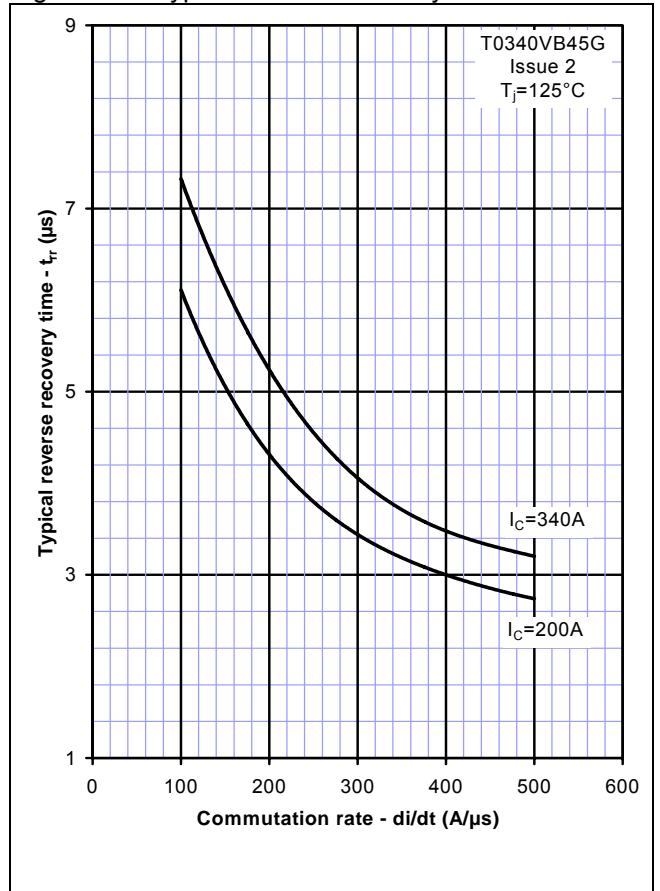


Figure 15 – Transient thermal impedance (IGBT)

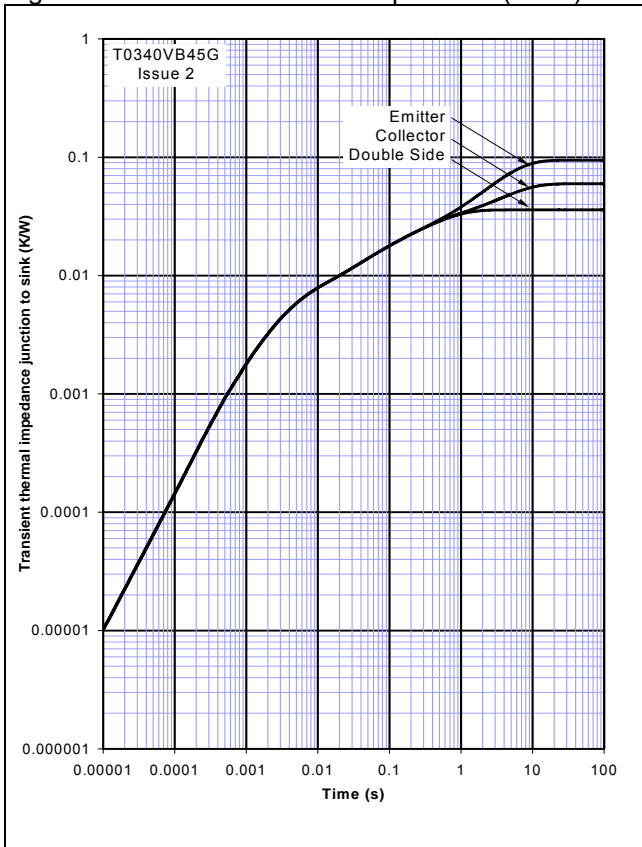
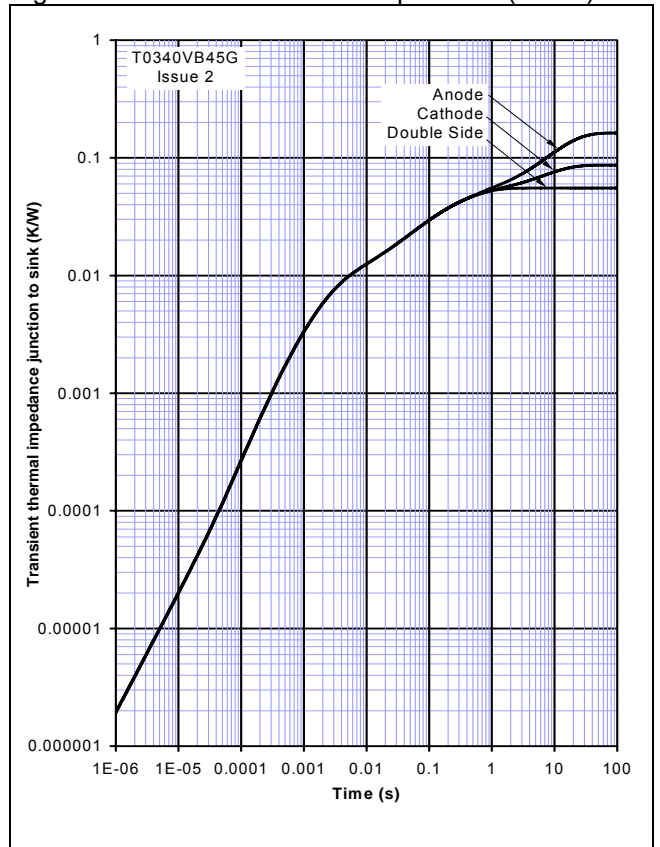
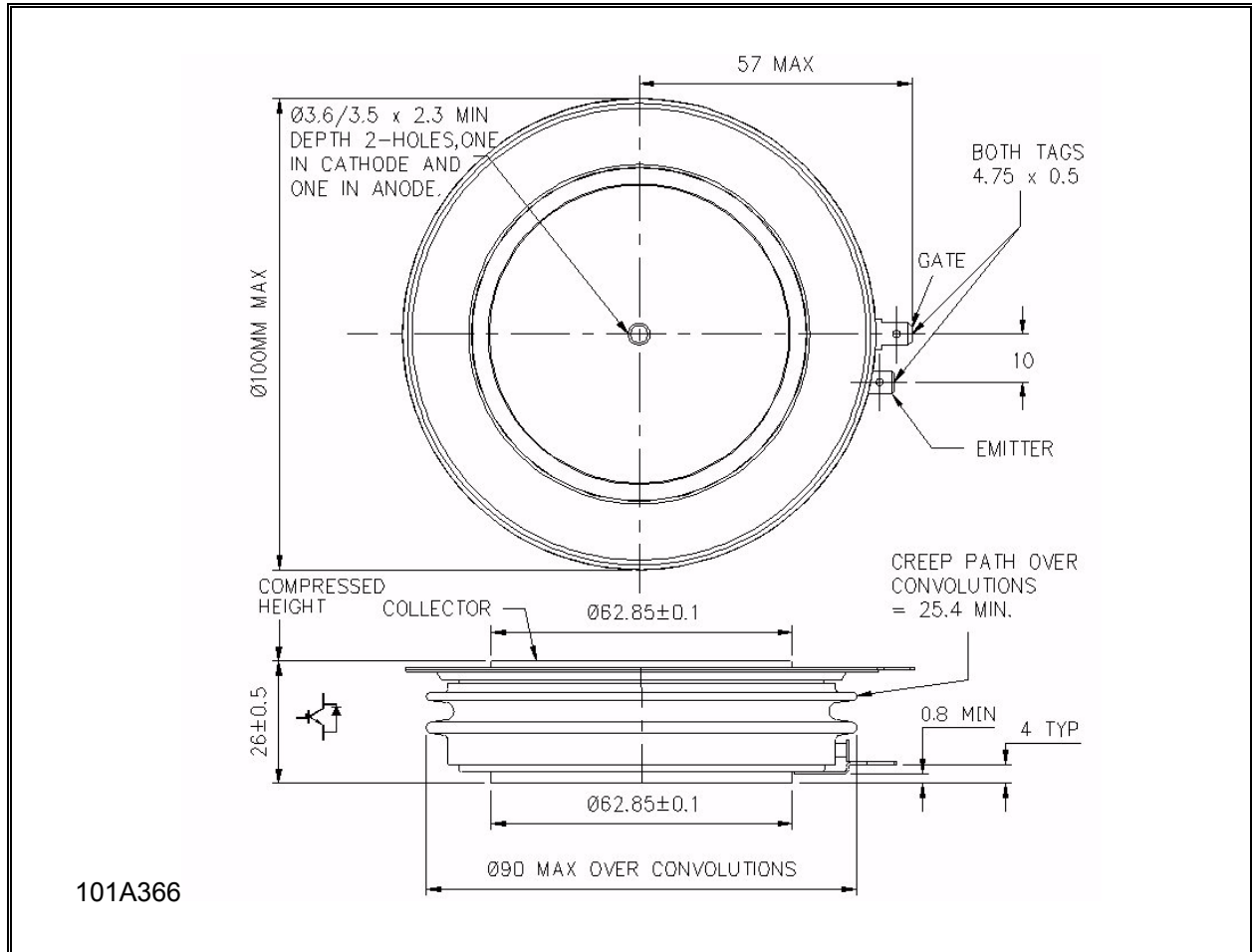


Figure 16 – Transient thermal impedance (Diode)



Outline Drawing & Ordering Information



ORDERING INFORMATION

(Please quote 10 digit code as below)

T0340	VB	45	G
Fixed type Code	Fixed Outline Code	Voltage Grade $V_{CES}/100$ 45	Fixed format code

Typical order code: T0340VB45G ($V_{CES} = 4500V$)

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